L Number	Hits	Search Text	DB	Time stamp
-	12	(("6429063") or ("6417044") or ("6399441")	USPAT	2003/09/16 09:12
		or ("6395590") or ("6372564") or		
		("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or		
		("6518125") or ("6482708")).PN.		
_	2	((nitride adj read adj only adj memory) or	USPAT;	2003/09/02 14:33
	Ì	(nitride adj (read-only) adj memory)) and	US-PGPUB;	
		(ono same (wet adj etching) same (dop\$6 or	EPO; JPO;	
		implant\$6) same (buried adj bit adj line))	DERWENT; IBM TDB	
l _	2	(ono same (wet adj etching) same (dop\$6 or	USPAT;	2003/09/02 14:12
		<pre>implant\$6) same (buried adj bit adj line))</pre>	US-PGPUB;	
		and ((nitride adj read adj only adj	EPO; JPO;	
		memory) or (nitride adj (read-only) adj memory))	DERWENT; IBM TDB	
_	3	((nitride adj read adj only adj memory) or	USPAT;	2003/09/02 14:15
		(nitride adj (read-only) adj memory)) and	US-PGPUB;	
ļ		ono and (wet adj etching) and (dop\$6 or	EPO; JPO;	
		implant\$6) and (buried adj bit adj line)	DERWENT;	
_	8	((nitride adj read adj only adj memory) or	IBM_TDB USPAT;	2003/09/02 14:27
		(nitride adj (read-only) adj memory)) and	US-PGPUB;	=====================================
		ono and (wet adj etching) and (dop\$6 or	EPO; JPO;	
		implant\$6) and (bit adj line)	DERWENT;	
_	94	 ((nitride adj read adj only adj memory) or	IBM_TDB USPAT;	2003/09/02 14:33
_	94	(nitride adj (read-only) adj memory)) and	US-PGPUB;	2003/03/02 14.33
		ono and (dop\$6 or implant\$6)	EPO; JPO;	
			DERWENT;	
	0.4		IBM_TDB	2003/09/02 14:34
-	94	<pre>(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory))</pre>	USPAT; US-PGPUB;	2003/09/02 14:34
		and ono and (dop\$6 or implant\$6)) and	EPO; JPO;	
		@ad<=20021115	DERWENT;	
			IBM_TDB	2002/00/02 14 20
_	81	<pre>((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory))</pre>	USPAT; US-PGPUB;	2003/09/02 14:29
		and ono and (dop\$6 or implant\$6)) and	EPO; JPO;	
		@ad<=20021115) and bit	DERWENT;	
-	7.0		IBM TDB	2003/09/02 14:34
_	72	<pre>((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory))</pre>	USPAT; US-PGPUB;	2003/09/02 14:34
		and ono and (dop\$6 or implant\$6)) and	EPO; JPO;	
		@ad<=20021115) and (bit adj line)	DERWENT;	
		//	IBM_TDB	2002/00/02 14 22
_	2	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or	USPAT; US-PGPUB;	2003/09/02 14:33
		nrom) and (ono same (wet adj etching) same	EPO; JPO;	
		(dop\$6 or implant\$6) same (buried adj bit	DERWENT;	
	1.55	adj line))	IBM_TDB	2002/00/02 14-22
-	157	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or	USPAT; US-PGPUB;	2003/09/02 14:33
	1	NROM) and ono and (dop\$6 or implant\$6)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000 /00 /00 04 05
-	150	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or	USPAT; US-PGPUB;	2003/09/02 14:34
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115	DERWENT;	
			IBM_TDB	0000 /00 /00 5 5 5 5
-	115	<pre>((((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or</pre>	USPAT; US-PGPUB;	2003/09/02 14:46
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bit adj line)	DERWENT;	
			IBM_TDB	0000/05/00 55 /5
-	85	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
		or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6))	US-PGPUB; EPO; JPO;	
		and @ad<=20021115) and (bit adj line)) and	DERWENT;	
		(etch\$5)	IBM TDB	

_	24	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:48
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and ono and (dop\$6 or implant\$6)) and @ad<=20021115) and (bit adj line)) and	EPO; JPO; DERWENT;	
		(wet adj etch\$5)	IBM TDB	
_	30	((((nitride adj read adj only adj memory)	USPĀT;	2003/09/02 14:47
	30	or (nitride adj (read-only) adj memory) or	US-PGPUB;	2000,00,00
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
		line)	IBM_TDB	
_	6	(((((nitride adj read adj only adj	USPAT;	2003/09/02 14:47
		memory) or (nitride adj (read-only) adj	US-PGPUB;	
		memory) or NROM) and one and (dop\$6 or	EPO; JPO;	
		implant\$6)) and @ad<=20021115) and (bit	DERWENT;	
		adj line)) and (wet adj etch\$5)) and (bur\$4 adj bit adj line)	IBM_TDB	
1_	6	(((((nitride adj read adj only adj memory)	USPAT;	2003/09/02 14:49
_		or (nitride adj (read-only) adj memory) or	US-PGPUB;	2000,03,02 21113
		NROM) and ono and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
		line)) and (wet adj etch\$5)	IBM_TDB	
-	26	(((((nitride adj read adj only adj memory)	USPĀT;	2003/09/03 07:57
		or (nitride adj (read-only) adj memory) or	US-PGPUB;	
		NROM) and one and (dop\$6 or implant\$6))	EPO; JPO;	
		and @ad<=20021115) and (bur\$4 adj bit adj	DERWENT;	
		line)) and (etch\$5)	IBM_TDB	2003/09/03 10:52
-	99	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or	USPAT; US-PGPUB;	2003/03/03 10:32
		(NROM)) and ((ono or (oxide adj nitride	EPO; JPO;	
		adj oxide) or ((silicon adj oxide) adj	DERWENT;	
	1	(silicon adj nitride) adj (silicon adj	IBM TDB	
		oxide))) and (dop\$6 or implant\$6) and		
		@ad<=20021115) and (bit adj line) and		
		(word adj line)		
-	1	("6566203").PN.	USPAT	2003/09/03 12:50
-	1	("6461906").PN.	USPAT	2003/09/03 13:17
-	1	("5496753").PN.	USPAT	2003/09/03 13:07
-	329	(438/261).CCLS.	USPAT;	2003/09/03 13:07
	1		US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1390	(438/257).CCLS.	USPAT;	2003/09/03 13:09
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/00 15 5
-	578	(438/258).CCLS.	USPAT;	2003/09/03 13:08
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	330	(438/259).CCLS.	USPAT;	2003/09/03 13:08
		(100/200).0000.	US-PGPUB;	-555, 55, 55 15.00
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	98	(438/260).CCLS.	USPAT;	2003/09/03 13:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/420 /261 \	IBM_TDB	2002/00/02 12:00
-	329	(438/261).CCLS.	USPAT;	2003/09/03 13:08
			US-PGPUB; EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	199	(438/262).CCLS.	USPAT;	2003/09/03 13:08
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

				_
_	711	(438/526).CCLS.	USPAT;	2003/09/03 13:09
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	694	(438/275).CCLS.	USPAT;	2003/09/03 13:09
	0,3	(430/2/3/.0003.	US-PGPUB;	2003,03,03 13.03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	246	(438/294).CCLS.	USPĀT;	2003/09/03 13:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/00 10 10
-	152	(438/216).CCLS.	USPAT;	2003/09/03 13:10
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	333	(438/591).CCLS.	USPAT;	2003/09/03 13:10
	333	(430/391).0063.	US-PGPUB;	2003/03/03 13:10
1			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	152	(438/216).CCLS.	USPAT;	2003/09/03 13:10
		, , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	613	(438/264).CCLS.	USPAT;	2003/09/03 13:11
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	626	/400 /50D	IBM_TDB	0000/00/00 10 10
_	636	(438/527).CCLS.	USPAT;	2003/09/03 13:12
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	750	(438/287).CCLS.	USPAT;	2003/09/03 13:12
	, , , ,	(130/201/190201	US-PGPUB;	2000,00,00 13.12
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	74	(438/954).CCLS.	USPĀT;	2003/09/03 13:12
1			US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	20	semiconductor same ono same (etch\$4 adj	USPAT;	2003/09/03 15:28
		stop)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
l _	20	(semiconductor same ono same (etch\$4 adj	IBM_TDB USPAT;	2003/09/03 15:27
-	20	stop)) and @ad<=20021115	US-PGPUB;	2003/03/03 13.2/
		000p;	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	480	semiconductor and ono and (etch adj stop)	USPAT;	2003/09/15 14:21
		and @ad<=20021115	US-PGPUB;	
			EPO; JPO;	
i			DERWENT;	
			IBM_TDB	
-	12		USPAT;	2003/09/15 14:37
		adj stop) and @ad<=20021115	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

_	264	438/287,261,591.ccls. and ono and	USPAT;	2003/09/03 15:38
		@ad<=20021115	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	397	257/\$.ccls. and ono and (etch\$3 adj stop\$4	USPAT;	2003/09/15 14:52
		adj (layer or film)) and @ad<=20021115	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	340	438/\$.ccls. and ono and (etch\$3 adj stop\$4	USPAT;	2003/09/15 14:52
	330	adj (layer or film)) and @ad<=20021115	US-PGPUB;	2000, 03, 20 21.02
		auj (layer of film), and edax-20021115	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		and (atables add atable add (layer or	USPAT;	2003/09/15 14:53
_	502		US-PGPUB;	2003/03/13 14.33
!		film)) and @ad<=20021115		
			EPO; JPO;	
			DERWENT;	
		1,	IBM_TDB	2002/00/15 14:52
-	9	(ono same semiconductor same (etch\$3 adj	USPAT;	2003/09/15 14:53
	1	stop\$4 adj (layer or film))) and	US-PGPUB;	
		@ad<=20021115	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	478		USPAT;	2003/09/15 15:34
		stop\$4 adj (layer or film)) and	US-PGPUB;	
		@ad<=20021115	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	32968	liu.in.	USPĀT;	2003/09/15 15:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	10	liu.in. and cheng-jye	USPAT;	2003/09/15 15:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	2054	hsiung.in.	USPAT;	2003/09/15 15:36
1	2034	11024119.2111	US-PGPUB;	=====================================
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	66294	chen in	USPAT;	2003/09/15 15:36
-	00294	chen.in.	US-PGPUB;	2003/03/13 13.30
1			EPO; JPO;	
1			DERWENT;	
	_	1	IBM_TDB	2002/00/15 15:27
-	3	hsiung.in. and tai-liang	USPAT;	2003/09/15 15:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	32	chen.in. and chia-hsing	USPĀT;	2003/09/15 15:37
			US-PGPUB;	
j			EPO; JPO;	
1			DERWENT;	
			IBM TDB	